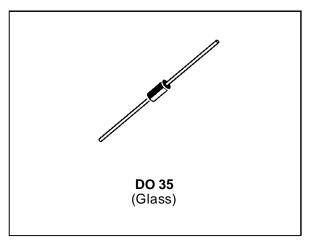


DB3 /DB4 / DC34

TRIGGER DIODES

FEATURES

- VBO: 32V / 34V / 40V VERSIONS
- LOW BREAKOVER CURRENT



DESCRIPTION

High reliability glass passivation insuring parameter stability and protection against junction contamination.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit	
Р	Power dissipation on printed circuit (L = 10 mm)	Ta = 65 °C	150	mW
I _{TRM}	Repetitive peak on-state current	tp = 20 μs F= 100 Hz	2	А
Tstg Tj	Storage and operating junction temperat	ure range	- 40 to + 125 - 40 to + 125	°C °C

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th (j-a)}	Junction to ambient	400	°C/W
Rth (j-I)	Junction-leads	150	°C/W

DB3 / DB4 / DC34

Symbol	Parameter	Test Conditions			Value		Unit
				DB3	DC34	DB4	
V _{BO}	Breakover voltage *	C = 22nF **	MIN	28	30	35	V
		see diagram 1	TYP	32	34	40	
			MAX	36	38	45	
[I+V _{BO} I-I-V _{BO} I]	Breakover voltage symmetry	C = 22nF ** see diagram 1	MAX		± 3		V
ΙΔV± Ι	Dynamic breakover voltage *	$\Delta I = [I_{BO} \text{ to } I_F=10\text{mA}]$ see diagram 1	MIN		5		V
Vo	Output voltage *	see diagram 2	MIN		5		V
I _{BO}	Breakover current *	C = 22nF **	MAX	100	50	100	μA
tr	Rise time *	see diagram 3	TYP		1.5		μs
IB	Leakage current *	$V_B = 0.5 V_{BO} max$ see diagram 1	MAX		10		μA

ELECTRICAL CHARACTERISTICS (Tj = 25° C)

* Electrical characteristic applicable in both forward and reverse directions.

** Connected in parallel with the devices.

DIAGRAM 1 : Current-voltage characteristics

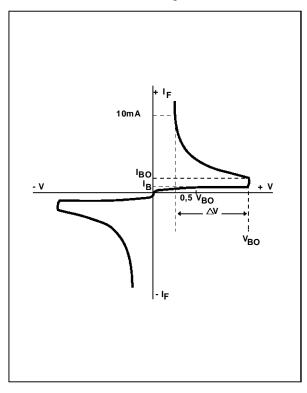
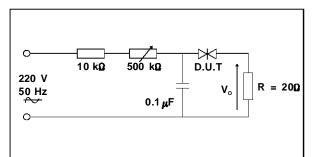
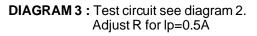
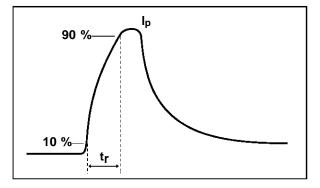


DIAGRAM 2 : Test circuit for output voltage









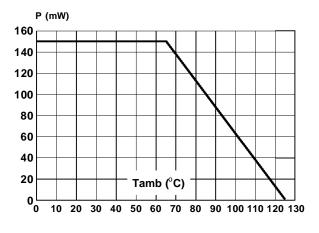


Fig.1 : Power dissipation versus ambient temperature (maximum values)

Fig.2 : Relative variation of V_{BO} versus junction temperature (typical values)

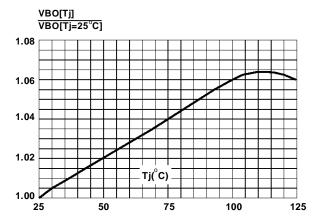
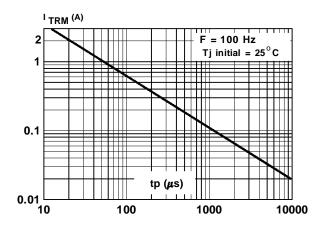


Fig.3: Peak pulse current versus pulse duration (maximum values)



DB3 / DB4 / DC34

PACKAGE MECHANICAL DATA (in millimeters) DO 35 Glass

		B not	e 1 ⊨ ↓ ØD		A B ØC
		-			
REF.			ISIONS		NOTES
REF.	Millin	DIMEN		hes	
REF.	Millin Min.				
REF.		neters	Inc	hes	
	Min.	neters Max.	Inc Min.	hes Max.	NOTES 1 - The lead diameter Ø D is not controlled over zone E 2 - The minimum axial lengh within which the device may be
A	Min. 3.050	neters Max.	Inc Min. 0.120	hes Max.	NOTES 1 - The lead diameter Ø D is not controlled over zone E
A	Min. 3.050 12.7	Max. 4.500	Inc Min. 0.120 0.500	hes Max. 0.117	NOTES 1 - The lead diameter Ø D is not controlled over zone E 2 - The minimum axial lengh within which the device may be

Cooling method by convection and conduction Marking : type number Weight : 0.15 g Polarity : N A Stud torque : N A

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